Final datasheet

EconoPIM™3 module with Trench/Fieldstop IGBT4 and emitter controlled 3 diode and NTC

Features

- Electrical features
  - V_{CES} = 650 V
  - $I_{C\ nom}$ = 100 A / I_{CRM} = 200 A
  - Increased blocking voltage capability up to 650 V
  - High short-circuit capability
  - $T_{vj,op}$ = 150°C
  - Trench IGBT 4
  - $V_{CE,sat}$ with positive temperature coefficient
- Mechanical features
  - Integrated NTC temperature sensor
  - Copper base plate
  - Solder contact technology
  - Standard housing

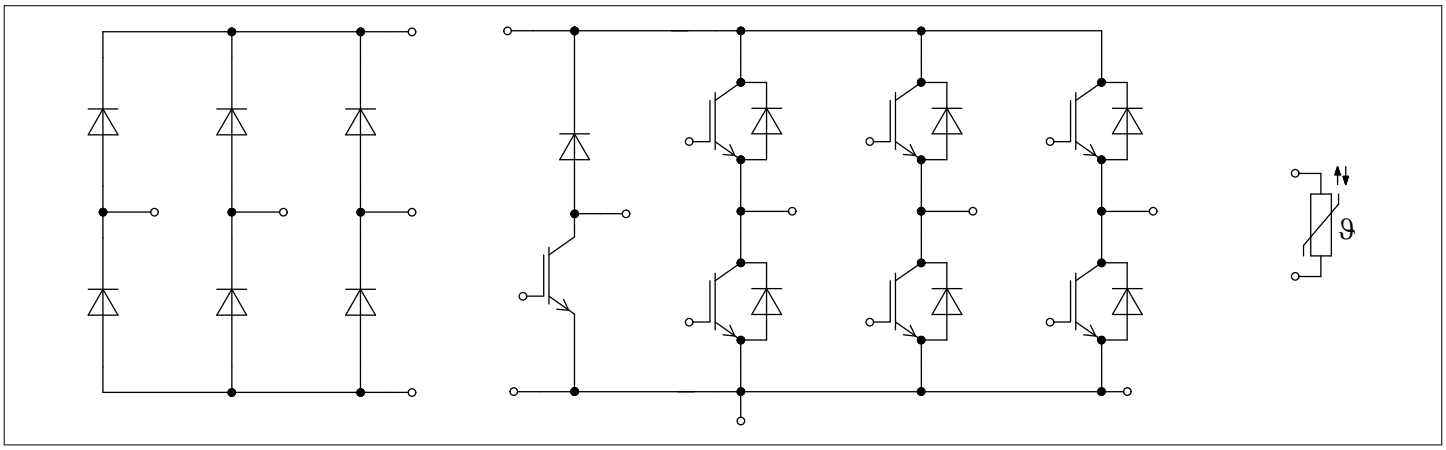
Potential applications

- Motor drives

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description



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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, f = 50 Hz, *t* = 1 min	2.5	kV
Material of module baseplate			Cu	
Internal isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Creepage distance	d_{Creep}	terminal to heatsink	10.0	mm
Clearance	d_{Clear}	terminal to heatsink	7.5	mm
Comparative tracking index	*CTI*		> 200	

Table 2 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Thermal resistance, case to heat sink	R_{thCH}	λ_{grease} = 1 W/(m·K)			0.009		K/W
Stray inductance module	L_{sCE}				40		nH
Module lead resistance, terminals - chip	$R_{AA'+CC'}$	T_C = 25 °C, per switch			2		mΩ
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	T_C = 25 °C, per switch			4		mΩ
Storage temperature	T_{stg}			-40		125	°C
Mounting torque for module mounting	*M*	- Mounting according to valid application note	M5, Screw	3		6	Nm
Weight	*G*				300		g

***Note**: for operation with Vge= 0V/+15V we recommend a Rgon,min of 24 ohms and a Rgoff,min of 24 ohms (see AN 2006-01)*

2 IGBT, Inverter

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CES}		T_{vj} = 25 °C	650	V
Continuous DC collector current	I_{CDC}	$T_{vj\,max}$ = 175 °C	T_C = 70 °C	100	A
Repetitive peak collector current	I_{CRM}	t_p limited by $T_{vj\,op}$		200	A
Gate-emitter peak voltage	V_{GES}			±20	V

Table 4 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\,sat}$	I_C = 100 A, V_{GE} = 15 V	T_{vj} = 25 °C		1.55	1.95	V
			T_{vj} = 125 °C		1.70		
			T_{vj} = 150 °C		1.75		
Gate threshold voltage	V_{GEth}	I_C = 1.6 mA, V_{CE} = V_{GE}, T_{vj} = 25 °C		5.05	5.80	6.45	V
Gate charge	Q_G	V_{GE} = ±15 V			1		µC
Internal gate resistor	R_{Gint}	T_{vj} = 25 °C			2		Ω
Input capacitance	C_{ies}	f = 1000 kHz, T_{vj} = 25 °C, V_{CE} = 25 V, V_{GE} = 0 V			6.2		nF
Reverse transfer capacitance	C_{res}	f = 1000 kHz, T_{vj} = 25 °C, V_{CE} = 25 V, V_{GE} = 0 V			0.19		nF
Collector-emitter cut-off current	I_{CES}	V_{CE} = 650 V, V_{GE} = 0 V	T_{vj} = 25 °C			1	mA
Gate-emitter leakage current	I_{GES}	V_{CE} = 0 V, V_{GE} = 20 V, T_{vj} = 25 °C				400	nA
Turn-on delay time (inductive load)	t_{don}	I_C = 100 A, V_{CC} = 300 V, V_{GE} = ±15 V, R_{Gon} = 3.3 Ω	T_{vj} = 25 °C		0.070		µs
			T_{vj} = 125 °C		0.080		
			T_{vj} = 150 °C		0.080		
Rise time (inductive load)	t_r	I_C = 100 A, V_{CC} = 300 V, V_{GE} = ±15 V, R_{Gon} = 3.3 Ω	T_{vj} = 25 °C		0.020		µs
			T_{vj} = 125 °C		0.020		
			T_{vj} = 150 °C		0.020		
Turn-off delay time (inductive load)	t_{doff}	I_C = 100 A, V_{CC} = 300 V, V_{GE} = ±15 V, R_{Goff} = 3.3 Ω	T_{vj} = 25 °C		0.260		µs
			T_{vj} = 125 °C		0.290		
			T_{vj} = 150 °C		0.300		
Fall time (inductive load)	t_f	I_C = 100 A, V_{CC} = 300 V, V_{GE} = ±15 V, R_{Goff} = 3.3 Ω	T_{vj} = 25 °C		0.070		µs
			T_{vj} = 125 °C		0.070		
			T_{vj} = 150 °C		0.070		
Turn-on energy loss per pulse	E_{on}	I_C = 100 A, V_{CC} = 300 V, L_σ = 30 nH, V_{GE} = ±15 V, R_{Gon} = 3.3 Ω, di/dt = 5100 A/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		0.33		mJ
			T_{vj} = 125 °C		0.77		
			T_{vj} = 150 °C		0.88		
Turn-off energy loss per pulse	E_{off}	I_C = 100 A, V_{CC} = 300 V, L_σ = 30 nH, V_{GE} = ±15 V, R_{Goff} = 3.3 Ω, dv/dt = 4000 V/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		3.5		mJ
			T_{vj} = 125 °C		4.7		
			T_{vj} = 150 °C		4.9		

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
SC data	I_{SC}	$V_{GE} \le 15$ V, $V_{CC} = 360$ V, $V_{CEmax}=V_{CES}-L_{sCE}*di/dt$	$t_P \le 10$ µs, $T_{vj}=25$ °C		480		A
			$t_P \le 10$ µs, $T_{vj}=150$ °C		380		
Thermal resistance, junction to case	R_{thJC}	per IGBT				0.450	K/W
Thermal resistance, case to heat sink	R_{thCH}	per IGBT, $\lambda_{grease} = 1$ W/(m·K)			0.140		K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		150	°C

3 Diode, Inverter

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		$T_{vj} = 25$ °C	650	V
Continuous DC forward current	I_F			100	A
Repetitive peak forward current	I_{FRM}	$t_P = 1$ ms		200	A
I^2t - value	I^2t	$t_P = 10$ ms, $V_R = 0$ V	$T_{vj} = 125$ °C	1100	A^2s
			$T_{vj} = 150$ °C	990	

Table 6 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 100$ A, $V_{GE} = 0$ V	$T_{vj} = 25$ °C		1.55	1.95	V
			$T_{vj} = 125$ °C		1.50		
			$T_{vj} = 150$ °C		1.45		
Peak reverse recovery current	I_{RM}	$V_{CC} = 300$ V, $I_F = 100$ A, $V_{GE} = -15$ V, $-di_F/dt = 5100$ A/µs ($T_{vj} = 150$ °C)	$T_{vj} = 25$ °C		130		A
			$T_{vj} = 125$ °C		150		
			$T_{vj} = 150$ °C		160		
Recovered charge	Q_r	$V_{CC} = 300$ V, $I_F = 100$ A, $V_{GE} = -15$ V, $-di_F/dt = 5100$ A/µs ($T_{vj} = 150$ °C)	$T_{vj} = 25$ °C		4		µC
			$T_{vj} = 125$ °C		8		
			$T_{vj} = 150$ °C		10		

(table continues...)

Table 6 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Reverse recovery energy	E_{rec}	V_{CC} = 300 V, I_F = 100 A, V_{GE} = -15 V, -di$_F$/dt = 5100 A/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		1.3		mJ
			T_{vj} = 125 °C		2.25		
			T_{vj} = 150 °C		2.75		
Thermal resistance, junction to case	R_{thJC}	per diode				0.800	K/W
Thermal resistance, case to heat sink	R_{thCH}	per diode, λ_{grease} = 1 W/(m·K)			0.250		K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		150	°C

4 Diode, Rectifier

Table 7 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		T_{vj} = 25 °C	1600	V
Maximum RMS forward current per chip	I_{FRMSM}	T_C = 80 °C		100	A
Maximum RMS current at rectifier output	I_{RMSM}	T_C = 80 °C		150	A
Surge forward current	I_{FSM}	t_P = 10 ms	T_{vj} = 25 °C	740	A
			T_{vj} = 150 °C	580	
I^2t - value	I^2t	t_P = 10 ms	T_{vj} = 25 °C	2750	A^2s
			T_{vj} = 150 °C	1700	

Table 8 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_F	I_F = 100 A	T_{vj} = 150 °C		1.10		V
Reverse current	I_r	T_{vj} = 150 °C, V_R = 1600 V			1		mA
Thermal resistance, junction to case	R_{thJC}	per diode				0.500	K/W
Thermal resistance, case to heat sink	R_{thCH}	per diode, λ_{grease} = 1 W/(m·K)			0.160		K/W
Temperature under switching conditions	$T_{vj,\,op}$			-40		150	°C

5 IGBT, Brake-Chopper

Table 9 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CES}		T_{vj} = 25 °C	650	V
Continuous DC collector current	I_{CDC}	$T_{vj\,max}$ = 175 °C	T_C = 80 °C	75	A
Repetitive peak collector current	I_{CRM}	t_p limited by $T_{vj\,op}$		150	A
Gate-emitter peak voltage	V_{GES}			±20	V

Table 10 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\,sat}$	I_C = 75 A, V_{GE} = 15 V	T_{vj} = 25 °C		1.55	1.95	V
			T_{vj} = 125 °C		1.70		
			T_{vj} = 150 °C		1.75		
Gate threshold voltage	V_{GEth}	I_C = 1.2 mA, V_{CE} = V_{GE}, T_{vj} = 25 °C		5	5.80	6.5	V
Gate charge	Q_G	V_{GE} = ±15 V			0.75		µC
Internal gate resistor	R_{Gint}	T_{vj} = 25 °C			0		Ω
Input capacitance	C_{ies}	f = 1000 kHz, T_{vj} = 25 °C, V_{CE} = 25 V, V_{GE} = 0 V			4.6		nF
Reverse transfer capacitance	C_{res}	f = 1000 kHz, T_{vj} = 25 °C, V_{CE} = 25 V, V_{GE} = 0 V			0.145		nF
Collector-emitter cut-off current	I_{CES}	V_{CE} = 650 V, V_{GE} = 0 V	T_{vj} = 25 °C			1	mA
Gate-emitter leakage current	I_{GES}	V_{CE} = 0 V, V_{GE} = 20 V, T_{vj} = 25 °C				400	nA
Turn-on delay time (inductive load)	t_{don}	I_C = 75 A, V_{CC} = 300 V, V_{GE} = ±15 V, R_{Gon} = 5.1 Ω	T_{vj} = 25 °C		0.025		µs
			T_{vj} = 125 °C		0.025		
			T_{vj} = 150 °C		0.025		
Rise time (inductive load)	t_r	I_C = 75 A, V_{CC} = 300 V, V_{GE} = ±15 V, R_{Gon} = 5.1 Ω	T_{vj} = 25 °C		0.020		µs
			T_{vj} = 125 °C		0.020		
			T_{vj} = 150 °C		0.020		
Turn-off delay time (inductive load)	t_{doff}	I_C = 75 A, V_{CC} = 300 V, V_{GE} = ±15 V, R_{Goff} = 5.1 Ω	T_{vj} = 25 °C		0.210		µs
			T_{vj} = 125 °C		0.240		
			T_{vj} = 150 °C		0.250		

(table continues...)

Table 10 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Fall time (inductive load)	t_f	I_C = 75 A, V_{CC} = 300 V, V_{GE} = ±15 V, R_{Goff} = 5.1 Ω	T_{vj} = 25 °C		0.060		µs
			T_{vj} = 125 °C		0.070		
			T_{vj} = 150 °C		0.070		
Turn-on energy loss per pulse	E_{on}	I_C = 75 A, V_{CC} = 300 V, L_σ = 30 nH, V_{GE} = ±15 V, R_{Gon} = 5.1 Ω, di/dt = 4000 A/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		0.385		mJ
			T_{vj} = 125 °C		0.55		
			T_{vj} = 150 °C		0.66		
Turn-off energy loss per pulse	E_{off}	I_C = 75 A, V_{CC} = 300 V, L_σ = 30 nH, V_{GE} = ±15 V, R_{Goff} = 5.1 Ω, dv/dt = 4000 V/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		3.35		mJ
			T_{vj} = 125 °C		3.9		
			T_{vj} = 150 °C		4.2		
SC data	I_{SC}	V_{GE} ≤ 15 V, V_{CC} = 360 V, V_{CEmax}=V_{CES}-L_{sCE}*di/dt	t_P ≤ 10 µs, T_{vj}=25 °C		360		A
			t_P ≤ 10 µs, T_{vj}=150 °C		290		
Thermal resistance, junction to case	R_{thJC}	per IGBT				0.600	K/W
Thermal resistance, case to heat sink	R_{thCH}	per IGBT, λ_{grease} = 1 W/(m·K)			0.190		K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		150	°C

6 Diode, Brake-Chopper

Table 11 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		T_{vj} = 25 °C	650	V
Continuous DC forward current	I_F			30	A
Repetitive peak forward current	I_{FRM}	t_P = 1 ms		60	A
I^2t - value	I^2t	t_P = 10 ms, V_R = 0 V	T_{vj} = 125 °C	90	A^2s
			T_{vj} = 150 °C	82	

Table 12 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_F	I_F = 30 A, V_{GE} = 0 V	T_{vj} = 25 °C		1.60	2.00	V
			T_{vj} = 125 °C		1.55		
			T_{vj} = 150 °C		1.50		
Peak reverse recovery current	I_{RM}	V_{CC} = 300 V, I_F = 30 A, -di$_F$/dt = 600 A/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		22		A
			T_{vj} = 125 °C		24		
			T_{vj} = 150 °C		27		
Recovered charge	Q_r	V_{CC} = 300 V, I_F = 30 A, -di$_F$/dt = 600 A/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		1.15		µC
			T_{vj} = 125 °C		2.3		
			T_{vj} = 150 °C		2.7		
Reverse recovery energy	E_{rec}	V_{CC} = 300 V, I_F = 30 A, -di$_F$/dt = 600 A/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		0.12		mJ
			T_{vj} = 125 °C		0.3		
			T_{vj} = 150 °C		0.36		
Thermal resistance, junction to case	R_{thJC}	per diode				1.80	K/W
Thermal resistance, case to heat sink	R_{thCH}	per diode, λ_{grease} = 1 W/(m·K)			0.570		K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		150	°C

7 NTC-Thermistor

Table 13 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	T_{NTC} = 25 °C		5		kΩ
Deviation of R_{100}	$\Delta R/R$	T_{NTC} = 100 °C, R_{100} = 493 Ω	-5		5	%
Power dissipation	P_{25}	T_{NTC} = 25 °C			20	mW
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298{,}15\ K))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2 - 1/(298{,}15\ K))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2 - 1/(298{,}15\ K))]$		3433		K

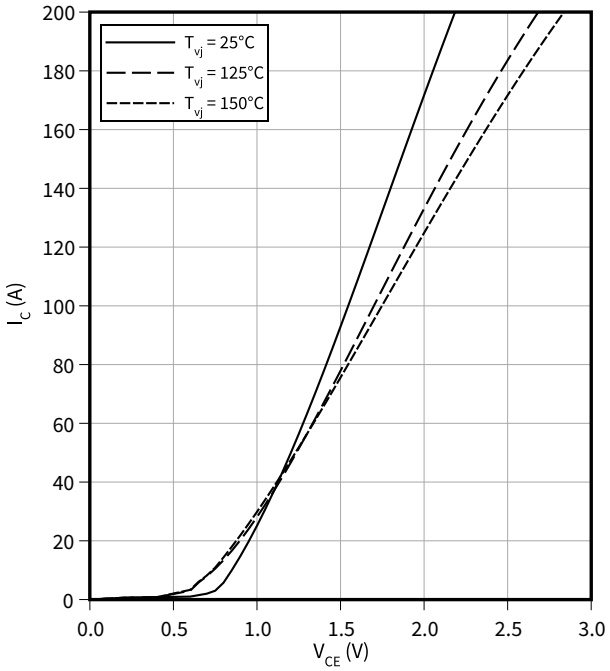
***Note**: Specification according to the valid application note.*

8 Characteristics diagrams

Output characteristic (typical), IGBT, Inverter

$I_C = f(V_{CE})$

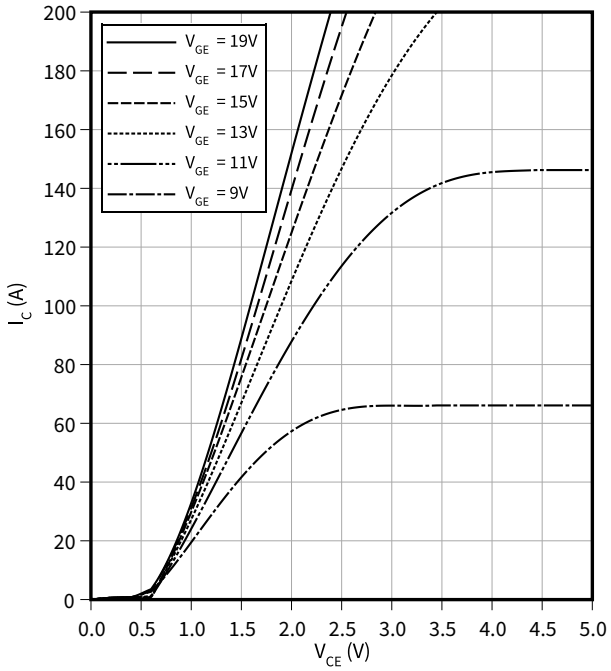
V_{GE} = 15 V



Output characteristic field (typical), IGBT, Inverter

$I_C = f(V_{CE})$

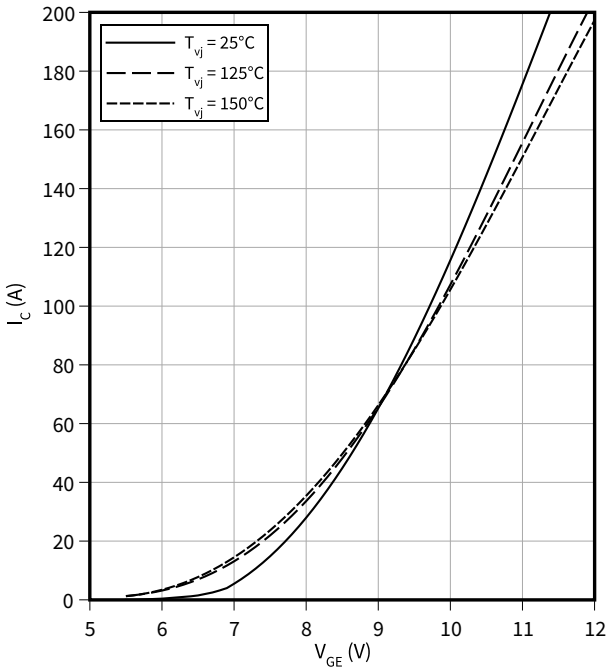
T_{vj} = 150 °C



Transfer characteristic (typical), IGBT, Inverter

$I_C = f(V_{GE})$

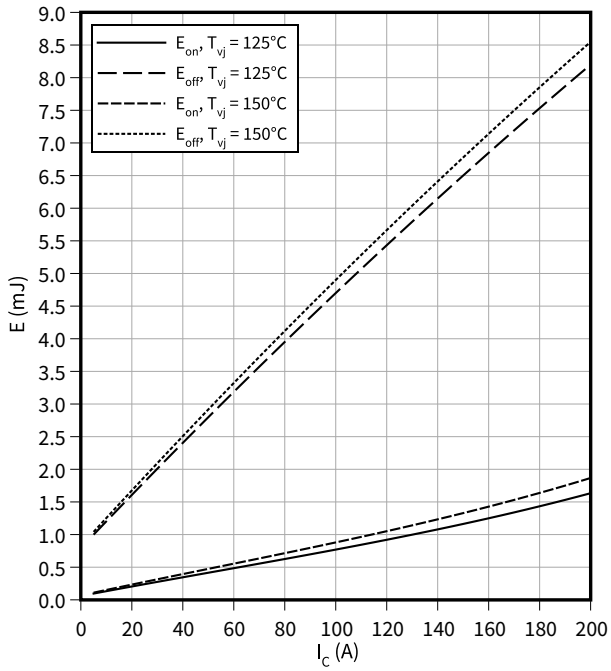
V_{CE} = 20 V



Switching losses (typical), IGBT, Inverter

$E = f(I_C)$

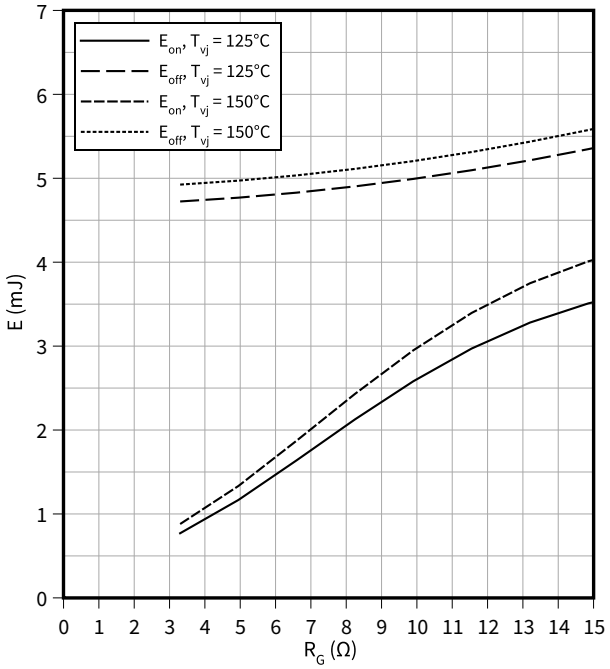
R_{Goff} = 3.3 Ω, R_{Gon} = 3.3 Ω, V_{GE} = ±15 V, V_{CC} = 300 V



Switching losses (typical), IGBT, Inverter

$E = f(R_G)$

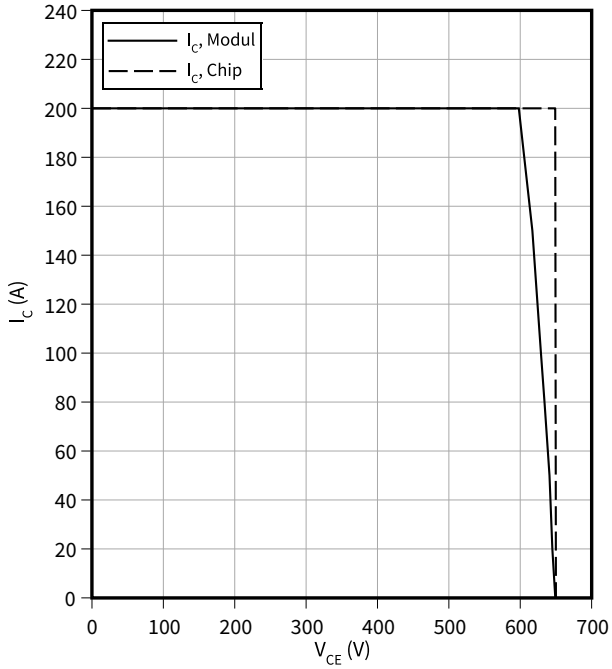
$V_{GE} = \pm 15$ V, $I_C = 100$ A, $V_{CC} = 300$ V



Reverse bias safe operating area (RBSOA), IGBT, Inverter

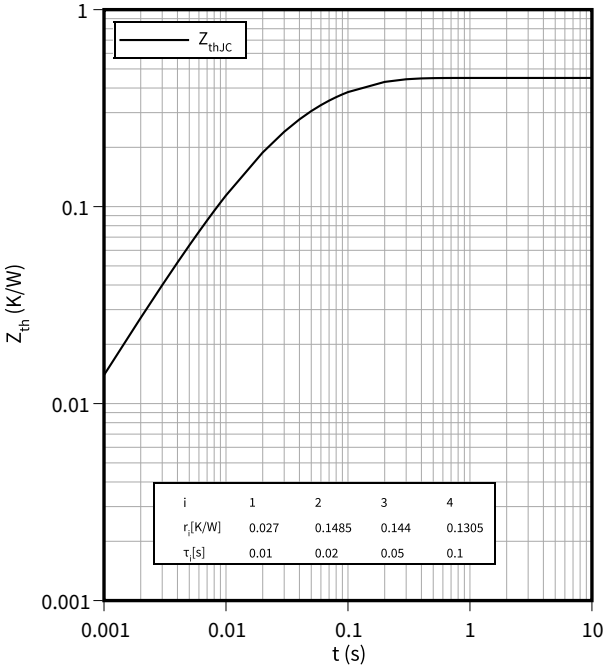
$I_C = f(V_{CE})$

$R_{Goff} = 3.3\ \Omega$, $V_{GE} = \pm 15$ V, $T_{vj} = 150$ °C



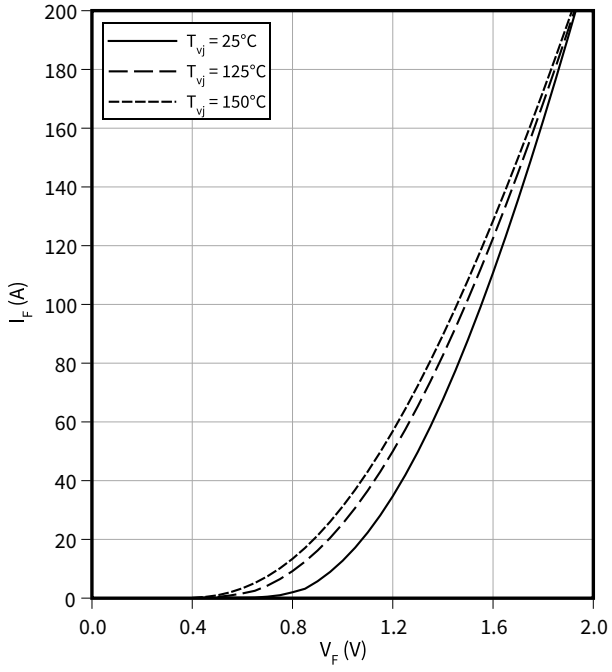
Transient thermal impedance, IGBT, Inverter

$Z_{th} = f(t)$



Forward characteristic (typical), Diode, Inverter

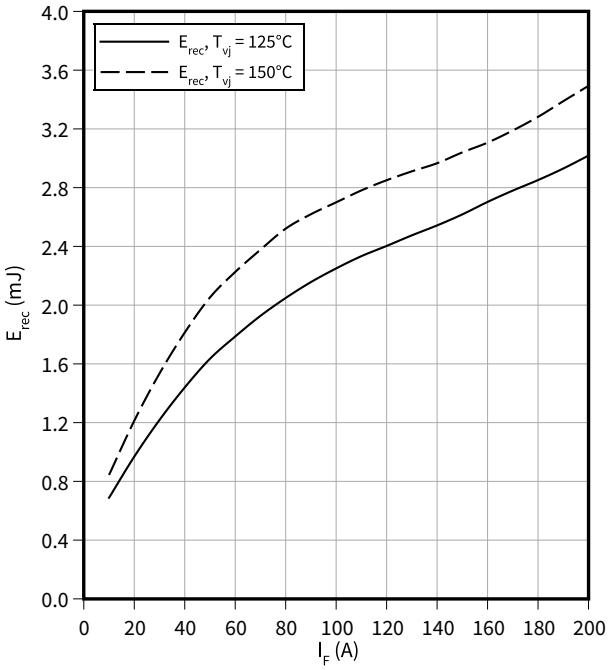
$I_F = f(V_F)$



Switching losses (typical), Diode, Inverter

$E_{rec} = f(I_F)$

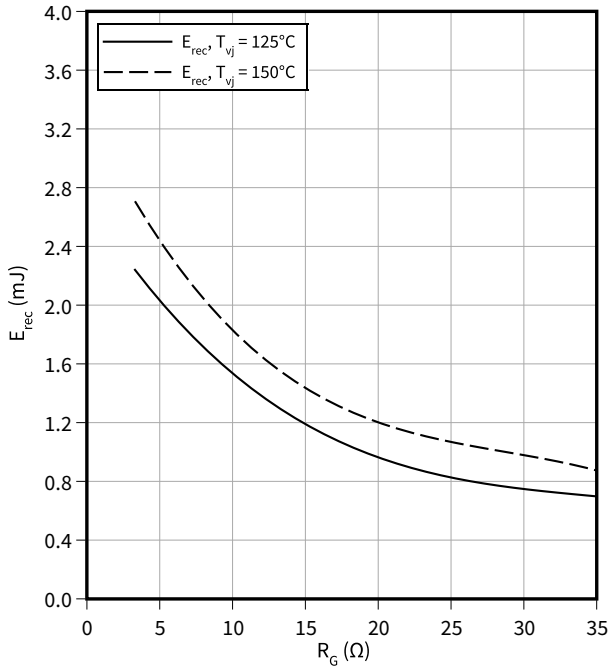
$V_{CE} = 300\ V$, $R_{Gon} = R_{Gon}(IGBT)$



Switching losses (typical), Diode, Inverter

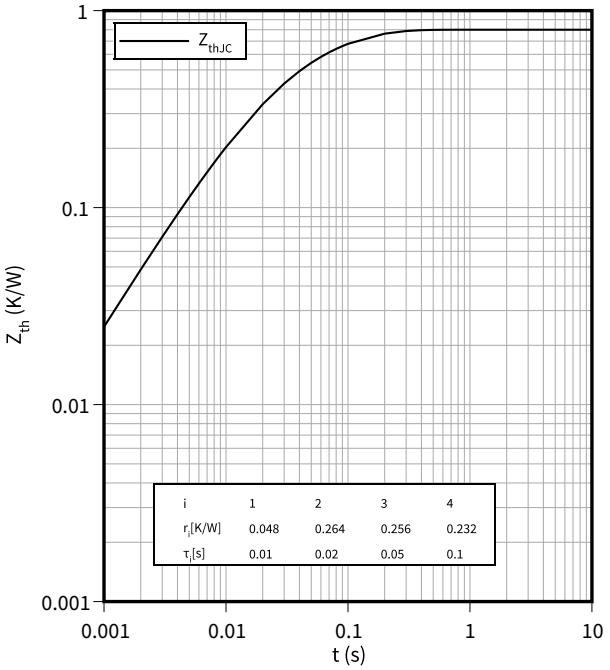
$E_{rec} = f(R_G)$

$V_{CE} = 300\ V$, $I_F = 100\ A$



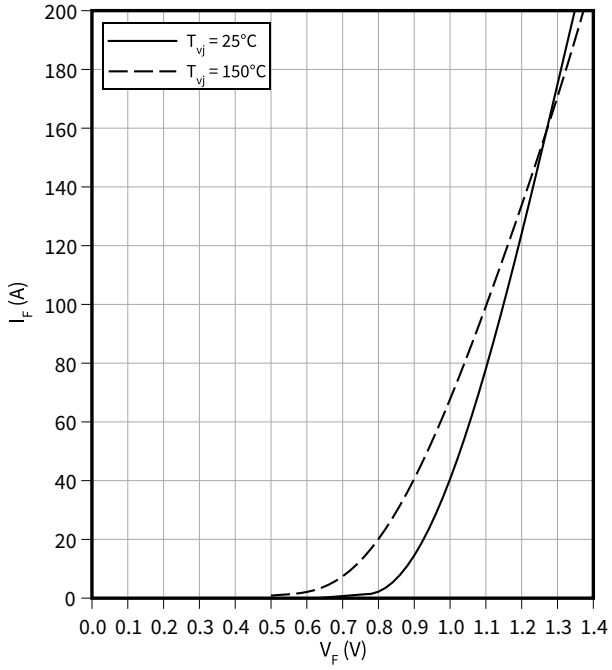
Transient thermal impedance, Diode, Inverter

$Z_{th} = f(t)$



Forward characteristic (typical), Diode, Rectifier

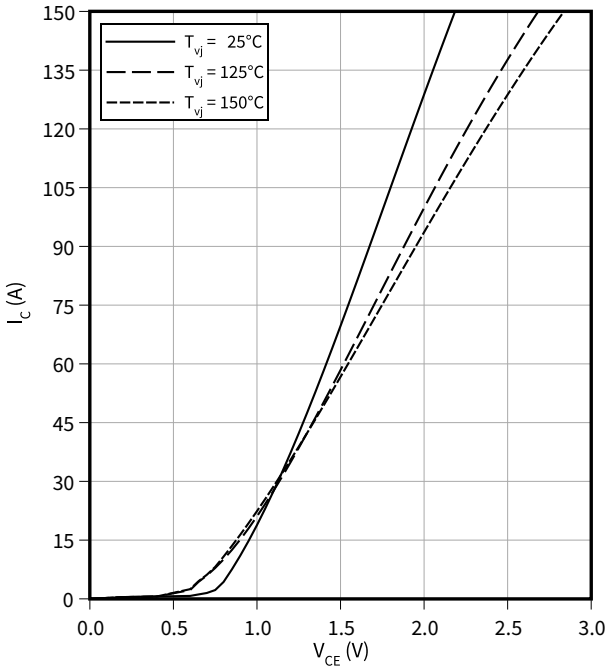
$I_F = f(V_F)$



Output characteristic (typical), IGBT, Brake-Chopper

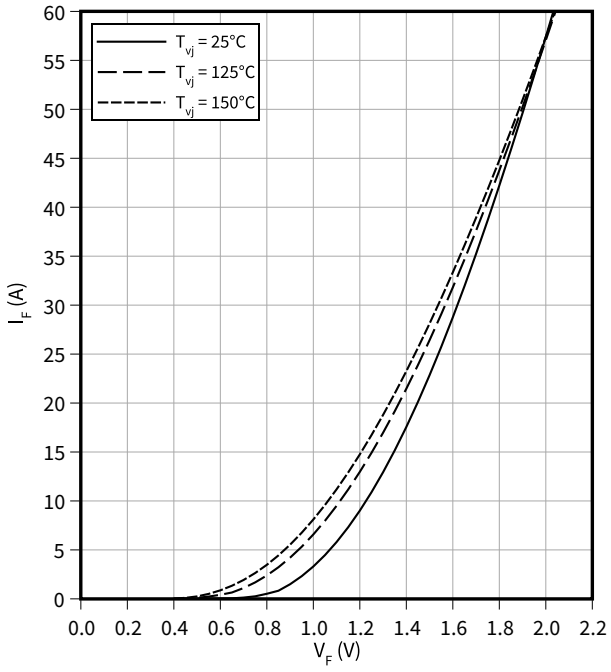
$I_C = f(V_{CE})$

$V_{GE} = 15$ V



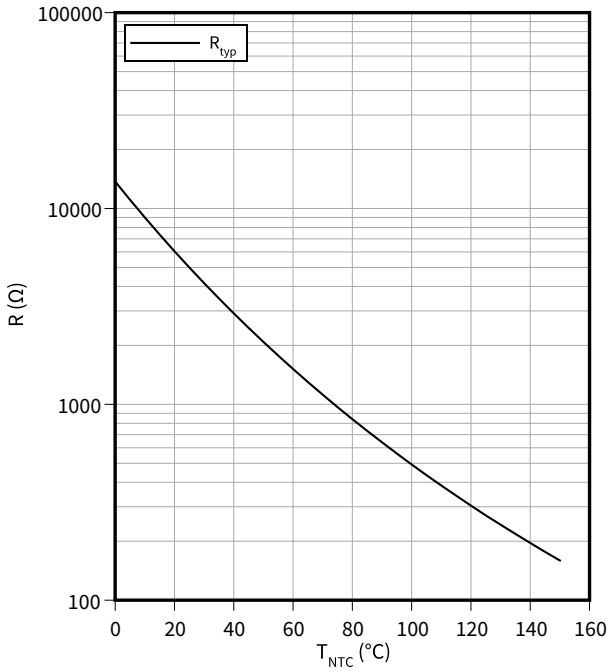
Forward characteristic (typical), Diode, Brake-Chopper

$I_F = f(V_F)$



Temperature characteristic (typical), NTC-Thermistor

$R = f(T_{NTC})$



9 Circuit diagram

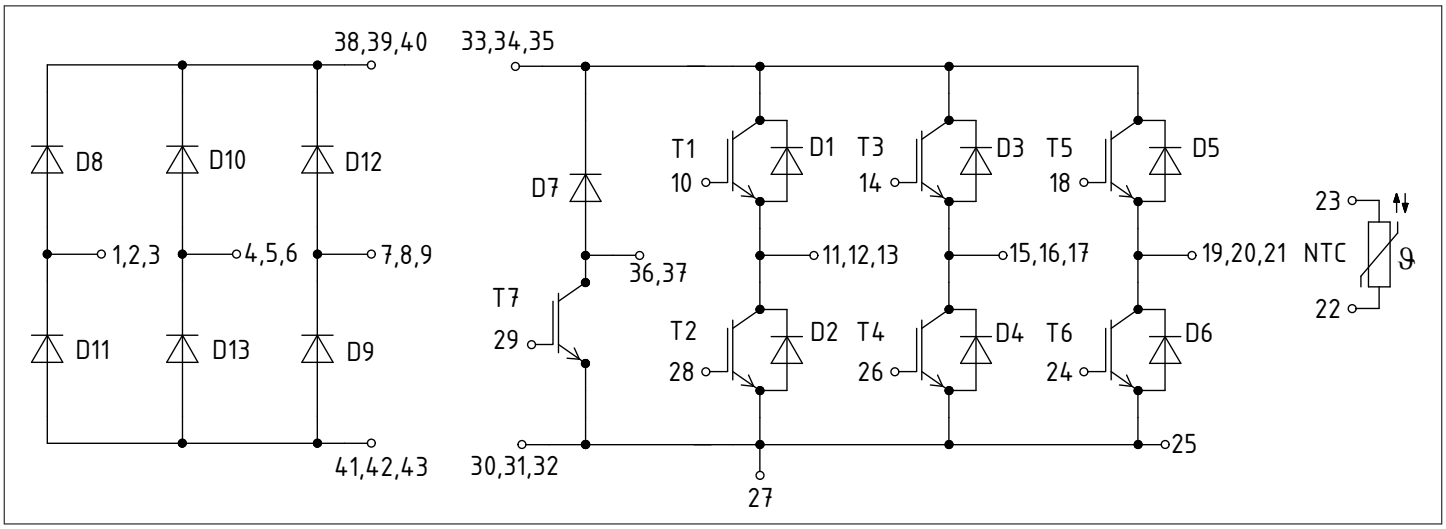


Figure 1

10 Package outlines

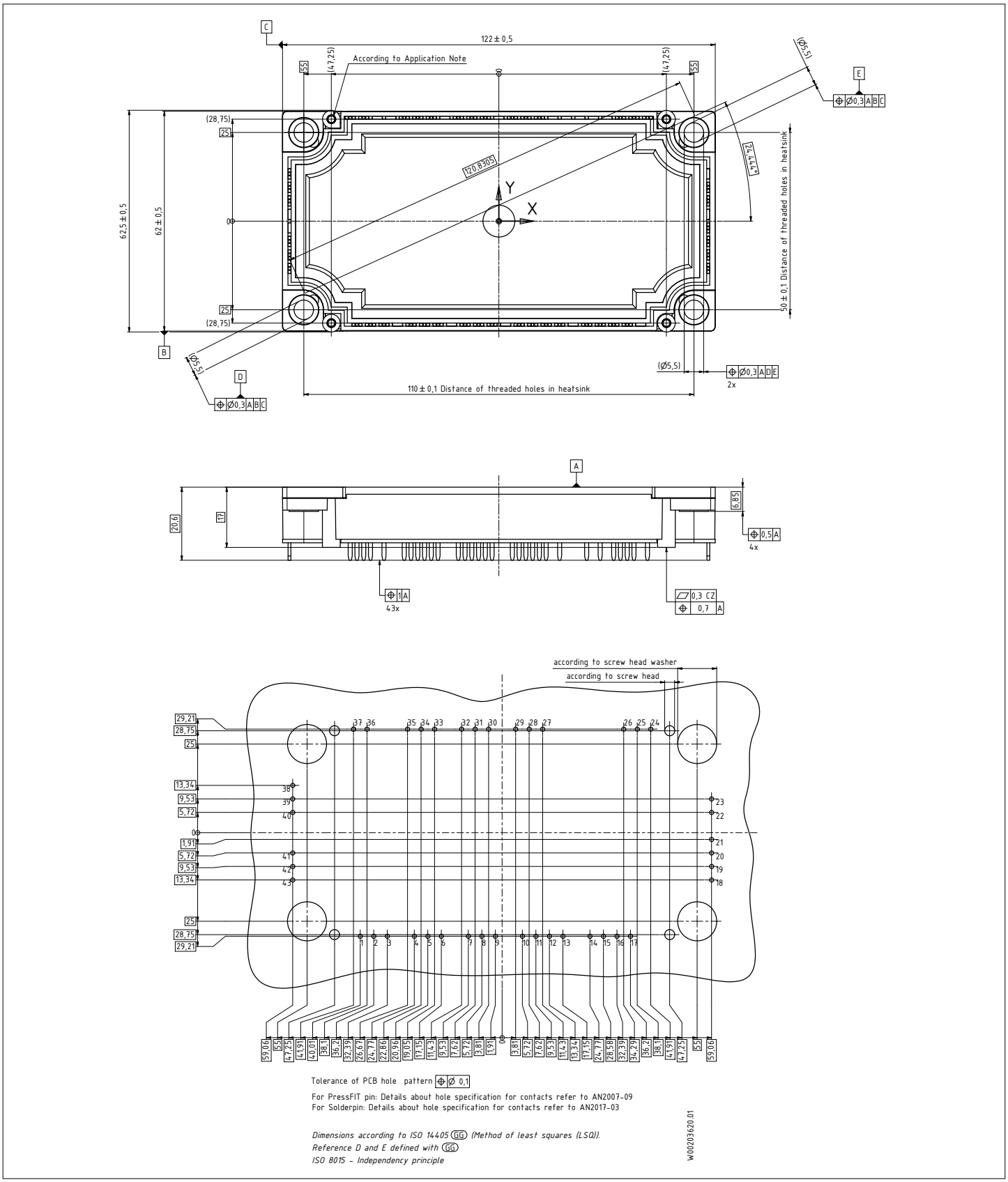


Figure 2

11 Module label code

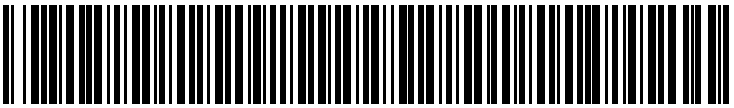
Module label code			
Code format	Data Matrix		Barcode Code128
Encoding	ASCII text		Code Set A
Symbol size	16x16		23 digits
Standard	IEC24720 and IEC16022		IEC8859-1
Code content	*Content* Module serial number Module material number Production order number Date code (production year) Date code (production week)	*Digit* 1 – 5 6 - 11 12 - 19 20 – 21 22 – 23	*Example* 71549 142846 55054991 15 30
Example	 71549142846550549911530	 71549142846550549911530	

Figure 3

Revision history

Document revision	Date of release	Description of changes
V2.0	2011-04-19	Preliminary datasheet
V2.1	2012-09-12	Preliminary datasheet
V3.0	2020-04-01	Final datasheet
n/a	2020-09-01	Datasheet migrated to a new system with a new layout and new revision number schema: target or preliminary datasheet = 0.xy; final datasheet = 1.xy
1.10	2024-08-27	Final datasheet

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